Andreas Hangleiter

List of Publications by Year
in descending order

256	5,860	108046	111975
papers	citations	37 h-index	67 g-index

257	257	257	3923
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Low-temperature internal quantum efficiency of GaInN/GaN quantum wells under steady-state conditions. Semiconductor Science and Technology, 2022, 37, 035017.	1.0	6
2	Ultrafast Terahertz Nanoseismology of GaInN/GaN Multiple Quantum Wells. Advanced Optical Materials, 2021, 9, 2100258.	3.6	8
3	Unity quantum efficiency in III-nitride quantum wells at low temperature: Experimental verification by time-resolved photoluminescence. Applied Physics Letters, 2021, 119, .	1.5	19
4	Pyramid Formation by Etching of InxGa1â^'xN/GaN Quantum Well Structures Grown on Nâ€face GaN for Nanooptical Light Emitters. Physica Status Solidi (B): Basic Research, 2021, 258, 2100085.	0.7	1
5	Plasma profiling time-of-flight mass spectrometry for fast elemental analysis of semiconductor structures with depth resolution in the nanometer range. Semiconductor Science and Technology, 2020, 35, 035006.	1.0	0
6	Reduced radiative emission for wide nonpolar III-nitride quantum wells. Physical Review B, 2019, 99, .	1.1	2
7	Recombination dynamics in GaInN/GaN quantum wells. Semiconductor Science and Technology, 2019, 34, 073002.	1.0	9
8	Microscopic analysis of interface composition dynamics in m-plane AlInN. Japanese Journal of Applied Physics, 2019, 58, SC1008.	0.8	2
9	Control of optical polarization properties by manipulation of anisotropic strain in nonpolar m-plane GaInN/GaN quantum wells. Applied Physics Letters, 2019, 114, .	1.5	6
10	Reduced nonradiative recombination in semipolar green-emitting III-N quantum wells with strain-reducing AlInN buffer layers. Applied Physics Letters, 2019, 115, 202103.	1.5	6
11	Internal quantum efficiency of nitride light emitters: a critical perspective. , 2018, , .		7
12	Indium incorporation into InGaN: The role of the adlayer. Journal of Crystal Growth, 2017, 464, 112-118.	0.7	4
13	Radiative recombination in polar, non-polar, and semi-polar III-nitride quantum wells. Proceedings of SPIE, 2017, , .	0.8	4
14	Strain dependence of In incorporation in m-oriented GaInN/GaN multi quantum well structures. Applied Physics Letters, 2016, 108, 102105.	1.5	7
15	Growth kinetics and island evolution during double-pulsed molecular beam epitaxy of InN. Journal of Applied Physics, 2016, 119, 235308.	1.1	2
16	Radiative and nonradiative recombination mechanisms in nonpolar and semipolar GaInN/GaN quantum wells. Physica Status Solidi (B): Basic Research, 2016, 253, 133-139.	0.7	17
17	Nonâ€and semipolar AlInN oneâ€dimensionally latticeâ€matched to GaN for realization of relaxed buffer layers for strain engineering in optically active GaNâ€based devices. Physica Status Solidi (B): Basic Research, 2016, 253, 84-92.	0.7	7
18	Insights into Interfacial Changes and Photoelectrochemical Stability of In_xGa_{1â€“x}N (0001) Photoanode Surfaces in Liquid Environments. ACS Applied Materials & Interfaces, 2016, 8, 8232-8238.	4.0	23

#	Article	IF	Citations
19	Efficient formation of excitons in a dense electron-hole plasma at room temperature. Physical Review B, 2015, 92, .	1.1	31
20	Efficiency droop in nitride LEDs revisited: impact of excitonic recombination processes. , 2015, , .		2
21	Indium incorporation processes investigated by pulsed and continuous growth of ultrathin InGaN quantum wells. Journal of Crystal Growth, 2015, 414, 49-55.	0.7	6
22	S shape in polar GaInN/GaN quantum wells: Piezoelectric-field-induced blue shift driven by onset of nonradiative recombination. Physical Review B, 2014, 90, .	1.1	35
23	Lattice-matched AlInN in the initial stage of growth. Applied Physics Letters, 2014, 104, .	1.5	14
24	Intentional anisotropic strain relaxation in (112Â¯2) oriented Al1âˆ'xInxN one-dimensionally lattice matched to GaN. Applied Physics Letters, 2014, 105, 122109.	1.5	5
25	Double-Pulsed Growth of InN by RF-MBE. Journal of Electronic Materials, 2013, 42, 849-853.	1.0	5
26	Atomic scale investigations of ultra-thin GaInN/GaN quantum wells with high indium content. Applied Physics Letters, 2013, 102, 102110.	1.5	21
27	Optimizing the growth process of the active zone in GaN based laser structures for the long wavelength region. Journal of Crystal Growth, 2013, 370, 105-108.	0.7	2
28	Measurement of the indium concentration in high indium content InGaN layers by scanning transmission electron microscopy and atom probe tomography. Applied Physics Letters, 2013, 102, 132112.	1.5	36
29	Nonradiative recombination due to point defects in GaInN/GaN quantum wells induced by Ar implantation. Proceedings of SPIE, 2013, , .	0.8	6
30	Strong enhancement of Eu+3 luminescence in europium-implanted GaN by Si and Mg codoping. Applied Physics Letters, 2013, 102, .	1.5	19
31	Transient THz photoconductivity in dynamically screened InGaN/GaN quantum wells. , 2013, , .		0
32	Strain-induced defects as nonradiative recombination centers in green-emitting GaInN/GaN quantum well structures. Applied Physics Letters, 2013, 103, .	1.5	69
33	Measuring composition in InGaN from HAADF-STEM images and studying the temperature dependence of Z-contrast. Journal of Physics: Conference Series, 2013, 471, 012009.	0.3	1
34	Room temperature excitonic recombination in GaInN/GaN quantum wells. Applied Physics Letters, 2013, 103, 202106.	1.5	45
35	Large optical polarization anisotropy due to anisotropic in-plane strain in m-plane GaInN quantum well structures grown on m-plane 6H-SiC. Applied Physics Letters, 2012, 100, .	1.5	18
36	Polarization of eigenmodes and the effect on the anisotropic gain in laser structures on nonpolar and semipolar GaN. Proceedings of SPIE, 2012, , .	0.8	0

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37	Growth optimization and characterization of lattice-matched Al0.82In0.18N optical confinement layer for edge emitting nitride laser diodes. Journal of Crystal Growth, 2012, 338, 20-29.	0.7	10
38	Nitrogen-polar core-shell GaN light-emitting diodes grown by selective area metalorganic vapor phase epitaxy. Applied Physics Letters, 2012, 101, .	1.5	29
39	Analysis of indium incorporation in non- and semipolar GaInN QW structures: comparing x-ray diffraction and optical properties. Semiconductor Science and Technology, 2012, 27, 024013.	1.0	18
40	Dielectric function and bowing parameters of InGaN alloys. Physica Status Solidi (B): Basic Research, 2012, 249, 485-488.	0.7	31
41	Auger recombination in GaInN/GaN quantum well laser structures. Applied Physics Letters, 2011, 99, .	1.5	57
42	Polarization dependent study of gain anisotropy in semipolar InGaN lasers. Applied Physics Letters, 2011, 99, .	1.5	7
43	Imposed layer-by-layer growth of ZnO on GaN/sapphire substrates using pulsed laser interval deposition. Thin Solid Films, 2011, 519, 7683-7685.	0.8	3
44	Indium incorporation in GaInN/GaN quantum well structures on polar and nonpolar surfaces. Physica Status Solidi (B): Basic Research, 2011, 248, 600-604.	0.7	15
45	Xâ€ray composition analysis of nonpolar GaInN/GaN multiple quantum well structures. Physica Status Solidi (B): Basic Research, 2011, 248, 616-621.	0.7	17
46	Spontaneous polarization field in polar and nonpolar GaInN/GaN quantum well structures. Physica Status Solidi (B): Basic Research, 2011, 248, 627-631.	0.7	6
47	Threeâ€dimensional GaN for semipolar light emitters. Physica Status Solidi (B): Basic Research, 2011, 248, 549-560.	0.7	62
48	Scanning nearâ€field luminescence microscopy of green light emitting GaInN/GaN quantum wells grown on câ€plane sapphire and on câ€plane bulk GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1556-1559.	0.8	1
49	Origin of the â€œgreen gapâ€• Increasing nonradiative recombination in indiumâ€rich GaInN/GaN quantum well structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2170-2172.	0.8	96
50	Growth of the active zone in nitride based long wavelength laser structures. Journal of Crystal Growth, 2011, 315, 250-253.	0.7	3
51	Growth and characterization of InGaN by RF-MBE. Journal of Crystal Growth, 2011, 323, 72-75.	0.7	29
52	Highly efficient light emission from stacking faults intersecting nonpolar GaInN quantum wells. Applied Physics Letters, 2011, 99, .	1.5	25
53	Correlated terahertz acoustic and electromagnetic emission in dynamically screened InGaN/GaN quantum wells. Physical Review B, 2011, 84, .	1.1	29
54	Cleaved-facet violet laser diodes with lattice-matched Al0.82In0.18N/GaN multilayers as n-cladding. Applied Physics Letters, 2011, 98, 201112.	1.5	6

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55	Effects of spontaneous polarization on GaInN/GaN quantum well structures. Journal of Applied Physics, 2011, 109, 123710.	1.1	10
56	Optical anisotropy in semipolar (Al,In)GaN laser waveguides. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1925-1927.	0.8	5
57	Recombination of free excitons in polar and nonpolar nitride quantum wells. Journal of Physics: Conference Series, 2010, 210, 012056.	0.3	0
58	Dislocation screening and strongly increased internal quantum efficiency in heteroepitaxial<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaN</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Al</mml:m Physical Review B, 2009, 79, .	1.1	8
59	AlInN optical confinement layers for edge emitting group IIIâ€nitride laser structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S897.	0.8	4
60	Towards green lasing: ingredients for a green laser diode based on GaInN. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S792.	0.8	3
61	Mechanism of thermal degradation in GaInN/GaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S594-S597.	0.8	9
62	Calculation of optical eigenmodes and gain in semipolar and nonpolar InGaN/GaN laser diodes. Physical Review B, 2009, 80, .	1.1	115
63	Properties of Mn-doped ZnO nanopowder. Applied Physics A: Materials Science and Processing, 2008, 91, 375-378.	1.1	5
64	Investigations of deep lying wide bandgap GaN and InGaN quantum well structures: A challenge for ellipsometric methods. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1378-1381.	0.8	0
65	High quality, high efficiency and ultrahigh In-content InGaN QWs â€“ the problem of thermal stability. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1662-1664.	0.8	10
66	Comparison of GaInN laser structures grown on different substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2277-2279.	0.8	2
67	Growth of QW structures with high indium concentration on -plane and -plane surfaces by MOVPE. Journal of Crystal Growth, 2008, 310, 4987-4991.	0.7	6
68	Indium incorporation dynamics into AlInN ternary alloys for laser structures lattice matched to GaN. Applied Physics Letters, 2008, 93, .	1.5	51
69	THE REASON FOR THE HIGH EMISSION EFFICIENCY OF GaInN/GaN BASED LEDS. International Journal of Modern Physics B, 2008, 22, 3261-3266.	1.0	1
70	Controlled low-temperature fabrication of ZnO nanopillars with a wet-chemical approach. Nanotechnology, 2007, 18, 195602.	1.3	25
71	Emission and recombination characteristics of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mi mathvariant="normal">Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow mathvariant="normal">In</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:mi mathvariant="normal">N</mml:mi><mml:mo>â•</mml:mo><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:m	1.1	59
72	Stark shift of interband transitions in AlNâ•GaN superlattices. Applied Physics Letters, 2007, 90, 241906.	1.5	8

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73	Anti-localization suppresses non-radiative recombination in GaInN/GaN quantum wells. Philosophical Magazine, 2007, 87, 2041-2065.	0.7	21
74	Aluminum incorporation in -layers and implications for growth optimization. Journal of Crystal Growth, 2007, 298, 361-366.	0.7	2
75	Vapour transport growth of ZnO nanorods. Applied Physics A: Materials Science and Processing, 2007, 88, 17-20.	1.1	16
76	Influence of excitons and electric fields on the dielectric function of GaN: Theory and experiment. Physical Review B, 2006, 74, .	1.1	22
77	Optimization scheme for the quantum efficiency of GaInN-based green-light-emitting diodes. Applied Physics Letters, 2006, 88, 071105.	1.5	59
78	Aqueous chemical growth and patterning of ZnO nanopillars on different substrate materials. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 992-996.	0.8	23
79	Catalyst-free vapor-phase transport growth of vertically aligned ZnO nanorods on 6H-SiC and (11-20)Al2O3. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1046-1050.	0.8	35
80	Critical points of the bandstructure of AlN/GaN superlattices investigated by spectroscopic ellipsometry and modulation spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2009-2013.	0.8	2
81	Optimizing the internal quantum efficiency of GaInN SQW structures for green light emitters. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1966-1969.	0.8	34
82	Investigations on oxygen diffusion in annealing processes of non-stoichiometric amorphous indium tin oxide thin films. Thin Solid Films, 2006, 513, 319-324.	0.8	18
83	Optical study of single InAs on In0.12Ga0.88As self-assembled quantum dots: biexciton binding energy dependence on the dots size. Applied Physics B: Lasers and Optics, 2006, 84, 317-322.	1.1	14
84	Vertically Increasing Well Thickness and In Content in GaInN MQW's due to V-shaped Pits. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	1
85	Experimental Analysis of the Spontaneous Polarization Field in GaN by UHV-cathodoluminescence. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	1
86	Large internal quantum efficiency of In-free UV-emitting GaNâˆ•AlGaN quantum-well structures. Applied Physics Letters, 2006, 88, 191108.	1.5	15
87	Specific emission characteristics of high-quantum-efficiency GaInN/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2712-2715.	0.8	0
88	Changes in excess carrier recombination dynamics caused by aging of GaN-based blue laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2708-2711.	0.8	0
89	Reflectance difference spectroscopy RDS/RAS combined with spectroscopic ellipsometry for a quantitative analysis of optically anisotropic materials. Physica Status Solidi (B): Basic Research, 2005, 242, 2617-2626.	0.7	7
90	Dielectric function and critical points of the band structure for AlGaN alloys. Physica Status Solidi (B): Basic Research, 2005, 242, 2610-2616.	0.7	38

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91	Localized high-energy emissions from the vicinity of defects in high-efficiencyGaxIn1âˆ'xNâˆ•GaNquantum wells. Physical Review B, 2005, 72, .	1.1	37
92	Determination of the polarization discontinuity at the AlGaNâˆ•GaN interface by electroreflectance spectroscopy. Applied Physics Letters, 2005, 86, 181912.	1.5	26
93	Suppression of Nonradiative Recombination by V-Shaped Pits inGaInN/GaNQuantum Wells Produces a Large Increase in the Light Emission Efficiency. Physical Review Letters, 2005, 95, 127402.	2.9	360
94	Recombination Mechanism in Short-Wavelength GaN/AlGaN Quantum Wells. Materials Research Society Symposia Proceedings, 2004, 831, 558.	0.1	1
95	Towards understanding the emission efficiency of nitride quantum wells. Physica Status Solidi A, 2004, 201, 2808-2813.	1.7	70
96	Narrow high-energy emission lines in high-resolution near-field spectroscopy on GaInN/GaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2520-2523.	0.8	8
97	Growth of AlxGa1âˆ'xN-layers on planar and patterned substrates. Journal of Crystal Growth, 2004, 272, 506-514.	0.7	5
98	Ultrafast polarization dynamics in optically excited biased quantum wells. , 2004, 5354, 151.		0
99	Influence of low-temperature interlayers on strain and defect density of epitaxial GaN layers. Journal of Crystal Growth, 2003, 248, 528-532.	0.7	6
100	Optical gain, gain saturation, and waveguiding in group III-nitride heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1860-1877.	0.8	8
101	Optical properties of nitride heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1816-1834.	0.8	21
102	Comparative study between laser performance and carrier lifetime of 400 nm emitting GaInN/GaN laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2304-2308.	0.8	3
103	High resolution near-field spectroscopy investigation of tilted InGaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2674-2677.	0.8	3
104	Growth of AlxGa1âˆ'xN and GaN on photo-electrochemically patterned SiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2072-2076.	0.8	3
105	Analysis of quantum efficiency of high brightness GaInN/GaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2202-2205.	0.8	16
106	Radiative and Nonradiative Recombination Times in Optically Excited GaInN/GaN Quantum Wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 324-328.	0.8	10
107	Correlation between Emission Spectra and Defect Position in InGaN-Based Light Emitting Devices. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 537-541.	0.8	2
108	Optimization of GaN/AlGaN Quantum Wells for Ultraviolet Emitters. Materials Research Society Symposia Proceedings, 2003, 798, 430.	0.1	0

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109	Ultrafast polarization dynamics in biased quantum wells under strong femtosecond optical excitation. Physical Review B, 2003, 68, .	1.1	56
110	Composition dependence of polarization fields in GaInN/GaN quantum wells. Applied Physics Letters, 2003, 83, 1169-1171.	1.5	97
111	High-resolution near-field spectroscopy investigation of GaN laterally overgrown structures on SiC. Applied Physics Letters, 2003, 82, 4071-4073.	1.5	1
112	Optical and structural anisotropy of InP/GaInP quantum dots for laser applications. Applied Physics Letters, 2003, 83, 887-889.	1.5	15
113	IIIâ€“V Nitrides: A New Age for Optoelectronics. MRS Bulletin, 2003, 28, 350-353.	1.7	17
114	Revealing the Defect Structure in Laterally Overgrown GaN Stripes Utilizing Photoelectrochemical Etching Techniques. Japanese Journal of Applied Physics, 2003, 42, 3381-3382.	0.8	0
115	Small-signal modulation response of InP/GaInP quantum-dot lasers. Applied Physics Letters, 2002, 80, 4015-4017.	1.5	13
116	Comment on â€œTunnel injection In0.4Ga0.6As/GaAs quantum dot lasers with 15 GHz modulation bandwidth at room temperatureâ€•[Appl. Phys. Lett. 80, 3482 (2002)]. Applied Physics Letters, 2002, 81, 2659-2660.	1.5	3
117	Optical gain in wide-bandgap group-III nitrides. , 2002, , .		1
118	Electron and Hole Confinement in GaInN/GaN and AlGaN/GaN Quantum Wells. Materials Research Society Symposia Proceedings, 2001, 693, 63.	0.1	2
119	Correlation of Defects and Local Bandgap Variations in GaInN/GaN/AlGaN LEDs. Physica Status Solidi (B): Basic Research, 2001, 228, 407-410.	0.7	3
120	Systematics of Optical Gain in GaInN/GaN Laser Structures. Physica Status Solidi A, 2001, 188, 59-63.	1.7	6
121	Analysis of the threshold current in nitride-based lasers. Journal of Crystal Growth, 2001, 230, 522-526.	0.7	10
122	First European GaN-Based Violet Laser Diode. Physica Status Solidi A, 2000, 180, 177-182.	1.7	16
123	Optical properties and polarization fields in the nitrides. Journal of Luminescence, 2000, 87-89, 130-134.	1.5	16
124	Lasing from excited states in self-assembled InP/GaInP quantum islands. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 263-268.	1.7	14
125	Growth of self-assembled InP quantum islands for red-light-emitting injection lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 482-490.	1.9	40
126	Internal electric fields in nitride-based heterostructures. , 2000, 3944, 58.		3

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127	Piezoelectric Field Effect on Optical Properties of GaN/GaInN/AlGaN Quantum Wells. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 628-633.	1.0	1
128	Birefringence in orderedGa0.47In0.53As/InP. Physical Review B, 1999, 59, 1582-1585.	1.1	4
129	Investigations on the performance of multiquantum barriers in short wavelength (630 nm) AlGaInP laser diodes. Applied Physics Letters, 1999, 74, 2158-2160.	1.5	17
130	Red Light Emitting Injection Lasers with Vertically-Aligned InP/GaInP Quantum Dots. Japanese Journal of Applied Physics, 1999, 38, 597-600.	0.8	11
131	Carrier confinement in GaInN/AlGaN/GaN quantum wells with asymmetric barriers: direction of the piezoelectric field. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 315-318.	1.7	12
132	Self-assembled InP quantum dots for red LEDs on Si and injection lasers on GaAs. Journal of Crystal Growth, 1999, 201-202, 1121-1125.	0.7	10
133	Direct Observation of Pyroelectric Fields in InGaN/GaN and AlGaN/GaN Heterostructures. Physica Status Solidi (B): Basic Research, 1999, 216, 405-408.	0.7	21
134	Optical Properties of Nitride Quantum Wells: How to Separate Fluctuations and Polarization Field Effects. Physica Status Solidi (B): Basic Research, 1999, 216, 427-430.	0.7	37
135	Investigations on the V-Defect Formation in GaInN-GaN Multi Quantum Well Structures. Physica Status Solidi (B): Basic Research, 1999, 216, 529-532.	0.7	6
136	Mode Conversion in GaN Based Laser Structures on Sapphire Due to the Birefringence of the Nitrides. Physica Status Solidi A, 1999, 176, 73-77.	1.7	4
137	Intra- and interwell transitions in GaInN/GaN multiple quantum wells with built-in piezoelectric fields. Applied Physics Letters, 1999, 74, 82-84.	1.5	67
138	Sign of the Piezoelectric Field in Asymmetric GaInN/AlGaN/GaN Single and Double Quantum Wells on SiC. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	0
139	Optical gain and waveguiding in GaN-based quantum well lasers. , 1999, 3625, 32.		0
140	Evidence for quantum-dot-like states in GaInN/GaN quantum wells?. Journal of Crystal Growth, 1998, 189-190, 597-600.	0.7	11
141	Determination of ordering induced birefringence in (Al)GaInP. Journal of Electronic Materials, 1998, 27, 122-126.	1.0	2
142	Ordering in GaInP: Is it relevant for devices?. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 8-14.	1.3	10
143	Reduction of oscillator strength due to piezoelectric fields inGaN/AlxGa1â^'xNquantum wells. Physical Review B, 1998, 57, R9435-R9438.	1.1	603
144	The role of piezoelectric fields in GaN-based quantum wells. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	134

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145	Optical Absorption and Excitation Spectroscopy on GaInN/GaN Double Heterostructures and Quantum Wells. Materials Science Forum, 1998, 264-268, 1287-1290.	0.3	1
146	Time-Resolved Spectroscopy on GaN/AlGaN Double Heterostructures and Quantum Wells. Materials Science Forum, 1998, 264-268, 1299-1302.	0.3	5
147	Valence-band splitting and band-gap reduction in ordered GaInAs/InP. Journal of Applied Physics, 1998, 83, 6196-6198.	1.1	9
148	Hole transport over heterobarriers in InP based multiple quantum well structures. Applied Physics Letters, 1998, 72, 1323-1325.	1.5	1
149	Red-light-emitting injection laser based on InP/GaInP self-assembled quantum dots. Applied Physics Letters, 1998, 73, 1784-1786.	1.5	60
150	Injection lasers with vertically aligned InP/GaInP quantum dots: Dependence of the threshold current on temperature and dot size. Applied Physics Letters, 1998, 73, 3730-3732.	1.5	21
151	Piezoelectric Field Effect on Optical Properties of GaN/GaInN/AlGaN Quantum Wells. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	2
152	Influence of p-doping and waveguide composition on the lasing properties of 630-nm band AlGaInP laser diodes. , 1998, , .		1
153	Red AlGaInP lasers: tunable and powerful. , 1998, , .		0
154	Dynamic properties of GaInP multielectrode ridge-waveguide lasers. Semiconductor Science and Technology, 1997, 12, 439-442.	1.0	5
155	Birefringence in ordered (Al)GaInP. Physical Review B, 1997, 55, 1730-1740.	1.1	26
156	Enhanced electroabsorption in tensile-strained GayIn1â^'yAs/AlxIn1â^'xAs/InP quantum well structures, due to field-induced merging of light-hole and heavy-hole transitions. Applied Physics Letters, 1997, 70, 2855-2857.	1.5	3
157	Single variant ordering in GaInAs/InP. Applied Physics Letters, 1997, 71, 2127-2129.	1.5	11
158	GaInN/GaN-Heterostructures and Quantum Wells Grown by Metalorganic Vapor-Phase Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 1997, 2, 1.	1.0	26
159	Effects of Piezoelectric Fields in GaInN/GaN and GaN/AlGaN Heterostructures and Quantum Wells. Materials Research Society Symposia Proceedings, 1997, 482, 557.	0.1	27
160	Intrinsic modulation bandwidth of strained GaInP/AlGaInP quantum well lasers. Applied Physics Letters, 1997, 71, 650-652.	1.5	8
161	Radiative carrier lifetime, momentum matrix element, and hole effective mass in GaN. Applied Physics Letters, 1997, 70, 631-633.	1.5	196
162	Control of monolayer terrace formation in selective epitaxy. Journal of Crystal Growth, 1997, 170, 695-699.	0.7	1

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163	Ordering in GaInP: epitaxy, basic characteristics and device relevance. III-Vs Review, 1997, 10, 38-42.	0.1	2
164	Optical gain in the nitrides: are there differences to other IIIâ€“V semiconductors?. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 201-206.	1.7	6
165	Relaxation of thermal strain in GaN epitaxial layers grown on sapphire. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 250-252.	1.7	11
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